

December 2011

FDZ663P

P-Channel 1.5 V Specified PowerTrench[®] Thin WL-CSP MOSFET -20 V, -2.7 A, 134 m Ω

Features

- Max $r_{DS(on)}$ = 134 m Ω at V_{GS} = -4.5 V, I_D = -2 A
- Max $r_{DS(on)} = 171 \text{ m}\Omega$ at $V_{GS} = -2.5 \text{ V}$, $I_D = -1.5 \text{ A}$
- Max $r_{DS(on)}$ = 216 m Ω at V_{GS} = -1.8 V, I_D = -1 A
- Max $r_{DS(on)}$ = 288 m Ω at V_{GS} = -1.5 V, I_D = -1 A
- Occupies only 0.64 mm² of PCB area. Less than 16% of the area of 2 x 2 BGA
- Ultra-thin package: less than 0.4 mm height when mounted to PCB
- RoHS Compliant

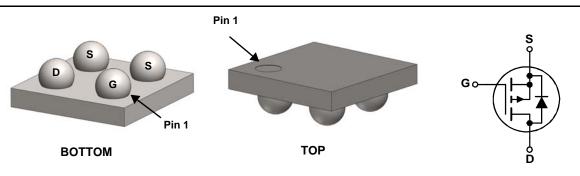


General Description

Designed on Fairchild's advanced 1.5 V PowerTrench[®] process with state of the art "fine pitch" Thin WLCSP packaging process, the FDZ663P minimizes both PCB space and $r_{\text{DS}(\text{on})}.$ This advanced WLCSP MOSFET embodies a breakthrough in packaging technology which enables the device to combine excellent thermal transfer characteristics, ultra-low profile (0.4 mm) and small (0.8x0.8 mm²) packaging, low gate charge, and low $r_{\text{DS}(\text{on})}.$

Applications

- Battery management
- Load switch
- Battery protection



WL-CSP 0.8X0.8 Thin

MOSFET Maximum Ratings TA = 25 °C unless otherwise noted

Symbol	Parar	Parameter			
V _{DS}	Drain to Source Voltage			-20	V
V_{GS}	Gate to Source Voltage			±8	V
	-Continuous	T _A = 25 °C	(Note 1a)	-2.7	۸
'D	-Pulsed			-10	— A
D	Power Dissipation	T _A = 25 °C	(Note 1a)	1.3	W
P_{D}	Power Dissipation	T _A = 25 °C	(Note 1b)	0.4	VV
T _J , T _{STG}	Operating and Storage Junction Tempe	rature Range		-55 to +150	°C

Thermal Characteristics

$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	(Note 1a)	93	°C/W
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	(Note 1b)	311	C/VV

Package Marking and Ordering Information

Device Marking	Device	Package	Reel Size	Tape Width	Quantity
EJ	FDZ663P	WL-CSP 0.8X0.8 Thin	7 "	8 mm	5000 units

Electrical Characteristics $T_J = 25$ °C unless otherwise noted

Symbol	Parameter	Test Conditions	Min	Тур	Max	Units
Off Chara	acteristics					
BV _{DSS}	Drain to Source Breakdown Voltage	$I_D = -250 \mu A, V_{GS} = 0 V$	-20			V
$\frac{\Delta BV_{DSS}}{\Delta T_{J}}$	Breakdown Voltage Temperature Coefficient	I_D = -250 μA, referenced to 25 °C		-14		mV/°C
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} = -16 V, V _{GS} = 0 V			-1	μΑ
I _{GSS}	Gate to Source Leakage Current	$V_{GS} = \pm 8 \text{ V}, V_{DS} = 0 \text{ V}$			±60	nA

On Characteristics

$V_{GS(th)}$	Gate to Source Threshold Voltage	$V_{GS} = V_{DS}, I_{D} = -250 \mu A$	-0.3	-0.7	-1.2	V
$\frac{\Delta V_{GS(th)}}{\Delta T_J}$	Gate to Source Threshold Voltage Temperature Coefficient	I_D = -250 μ A, referenced to 25 °C		2.4		mV/°C
		$V_{GS} = -4.5 \text{ V}, I_D = -2 \text{ A}$		103	134	
		$V_{GS} = -2.5 \text{ V}, I_D = -1.5 \text{ A}$		122	171	
r _{DS(on)}	r _{DS(on)} Static Drain to Source On Resistance	$V_{GS} = -1.8 \text{ V}, I_D = -1 \text{ A}$		149	216	mΩ
		$V_{GS} = -1.5 \text{ V}, I_D = -1 \text{ A}$		186	288	
		$V_{GS} = -4.5 \text{ V}, I_D = -2 \text{ A}, T_J = 125 ^{\circ}\text{C}$		137	198	
9 _{FS}	Forward Transconductance	$V_{DD} = -5 \text{ V}, I_D = -2 \text{ A}$		8		S

Dynamic Characteristics

C _{iss}	Input Capacitance	V 40.V.V 0.V	394	525	pF
C _{oss}	Output Capacitance	$V_{DS} = -10 \text{ V}, V_{GS} = 0 \text{ V},$ $f = 1 \text{ MHz}$	62	85	pF
C _{rss}	Reverse Transfer Capacitance	1 - 1 1011 12	53	80	pF

Switching Characteristics

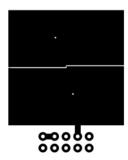
	•				
t _{d(on)}	Turn-On Delay Time		4.8	10	ns
t _r	Rise Time	$V_{DD} = -10 \text{ V}, I_D = -2.5 \text{ A},$	6.2	12	ns
t _{d(off)}	Turn-Off Delay Time	$V_{GS} = -4.5 \text{ V}, R_{GEN} = 6 \Omega$	67	107	ns
t _f	Fall Time		32	52	ns
Q_g	Total Gate Charge	45777	5.9	8.2	nC
Q_{gs}	Gate to Source Charge	$V_{GS} = -4.5 \text{ V}, V_{DD} = -10 \text{ V},$ $I_{D} = -2.5 \text{ A}$	0.6		nC
Q _{ad}	Gate to Drain "Miller" Charge	ID = -2.5 A	1.6		nC

Drain-Source Diode Characteristics

V_{SD}	Source to Drain Diode Forward Voltage	$V_{GS} = 0 \text{ V}, I_{S} = -1.4 \text{ A}$ (Note 2)	-0.8	-1.2	V
t _{rr}	Reverse Recovery Time	I _F = -2.5 A, di/dt = 100 A/μs	30	48	ns
Q _{rr}	Reverse Recovery Charge	TF = -2.5 A, α//αι = 100 A/μs	10	18	nC

Notes:

1. R_{6JA} is determined with the device mounted on a 1 in² pad 2 oz copper pad on a 1.5 x 1.5 in. board of FR-4 material. R_{6JC} is guaranteed by design while R_{6CA} is determined by the user's board design.



a. 93 °C/W when mounted on a 1 in² pad of 2 oz copper.



b. 311 °C/W when mounted on a minimum pad of 2 oz copper.

2. Pulse Test: Pulse Width < 300 μ s, Duty cycle < 2.0%.

Typical Characteristics T_J = 25 °C unless otherwise noted

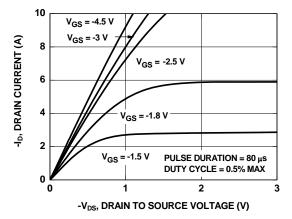


Figure 1. On-Region Characteristics

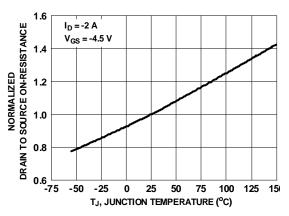


Figure 3. Normalized On-Resistance vs Junction Temperature

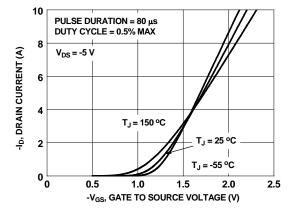


Figure 5. Transfer Characteristics

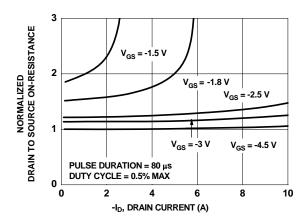


Figure 2. Normalized On-Resistance vs Drain Current and Gate Voltage

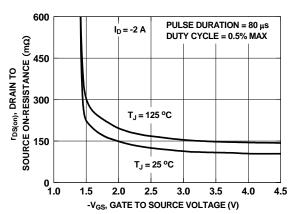


Figure 4. On-Resistance vs Gate to Source Voltage

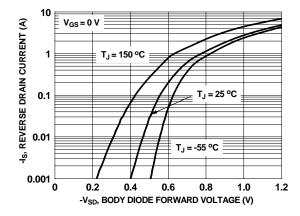


Figure 6. Source to Drain Diode Forward Voltage vs Source Current

Typical Characteristics T_J = 25 °C unless otherwise noted

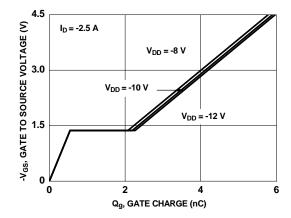


Figure 7. Gate Charge Characteristics

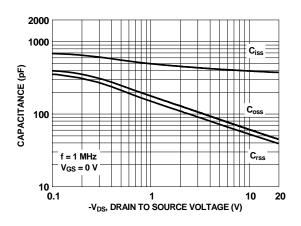


Figure 8. Capacitance vs Drain to Source Voltage

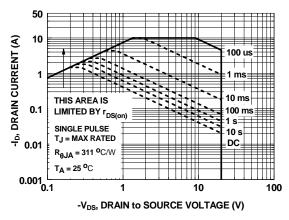


Figure 9. Forward Bias Safe Operating Area

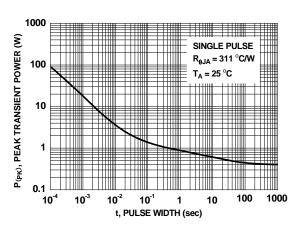


Figure 10. Single Pluse Maximum Power Dissipation

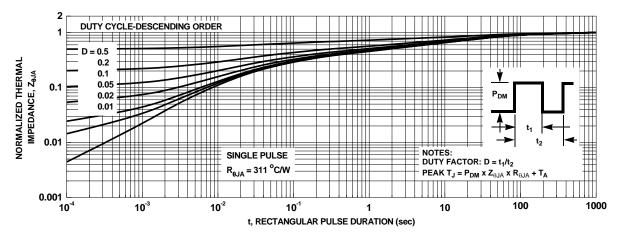
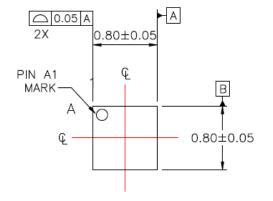
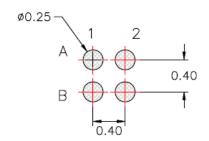


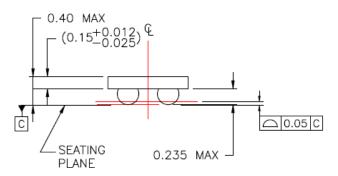
Figure 11. Junction-to-Ambient Transient Thermal Response Curve

Dimensional Outline and Pad Layout

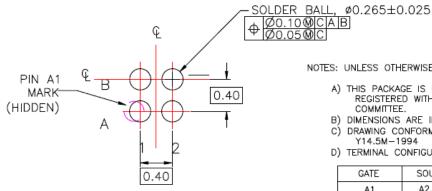




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LAND PATTERN RECOMMENDATION



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- C) DRAWING CONFORMS TO ASME Y14.5M-1994
- D) TERMINAL CONFIGURATION TABLE:

GATE	SOURCE	DRAIN
A1	A2, B2	B1





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